

N-Channel 60 V (D-S) MOSFET



FEATURES

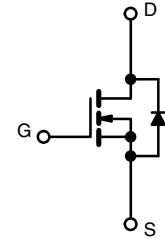
- TrenchFET® Gen IV power MOSFET
- 100 % R_g and UIS tested
- Material categorization: for definitions of compliance please see www.vishay.com/doc?99912



RoHS
COMPLIANT
HALOGEN
FREE

APPLICATIONS

- Synchronous rectification
- Primary side switch
- DC/DC converters
- Power supplies
- Motor drive control
- Battery and load switch



N-Channel MOSFET

PRODUCT SUMMARY

V _{DS} (V)	60
R _{DS(on)} max. (Ω) at V _{GS} = 10 V	0.0195
R _{DS(on)} max. (Ω) at V _{GS} = 4.5 V	0.0250
Q _g typ. (nC)	5.2
I _D (A)	11.3
Configuration	Single

ORDERING INFORMATION

Package	SO-8
Lead (Pb)-free and halogen-free	Si4850BDY-T1-GE3

ABSOLUTE MAXIMUM RATINGS (T_A = 25 °C, unless otherwise noted)

PARAMETER	SYMBOL	LIMIT	UNIT
Drain-source voltage	V _{DS}	60	V
Gate-source voltage	V _{GS}	± 20	V
Continuous drain current (T _J = 150 °C)	I _D	T _C = 25 °C	11.3
		T _C = 70 °C	9
		T _A = 25 °C	8.4 a, b
		T _A = 70 °C	6.8 a, b
Pulsed drain current (t = 100 μs)	I _{DM}	40	A
Continuous source-drain diode current	I _S	T _C = 25 °C	3.8
		T _A = 25 °C	2.1 a, b
Single pulse avalanche current	I _{AS}	15	
Single pulse avalanche energy	E _{AS}	11.3	mJ
Maximum power dissipation	P _D	T _C = 25 °C	4.5
		T _C = 70 °C	2.8
		T _A = 25 °C	2.5 a, b
		T _A = 70 °C	1.6 a, b
Operating junction and storage temperature range	T _J , T _{stg}	-55 to +150	°C
Soldering recommendations (peak temperature) ^c		260	

THERMAL RESISTANCE RATINGS

PARAMETER	SYMBOL	TYPICAL	MAXIMUM	UNIT
Maximum junction-to-ambient ^a	R _{thJA}	38	50	°C/W
Maximum junction-to-foot (drain)	R _{thJF}	22	28	

Notes

- Surface mounted on 1" x 1" FR4 board
- t = 10 s
- Maximum under steady state conditions is 85 °C/W

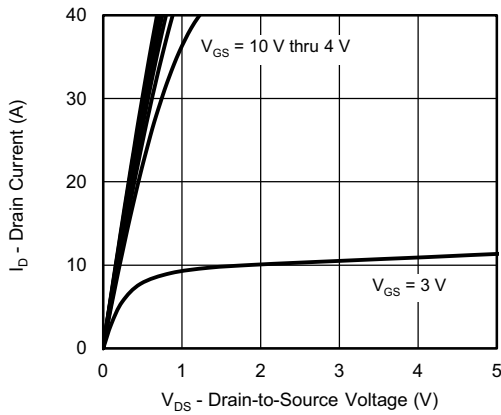
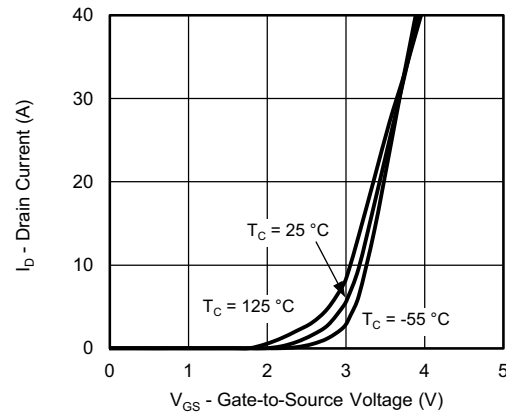
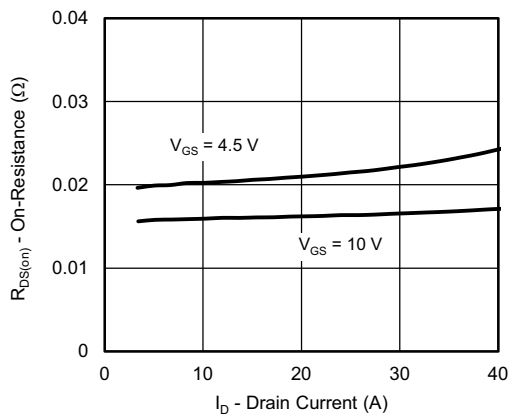
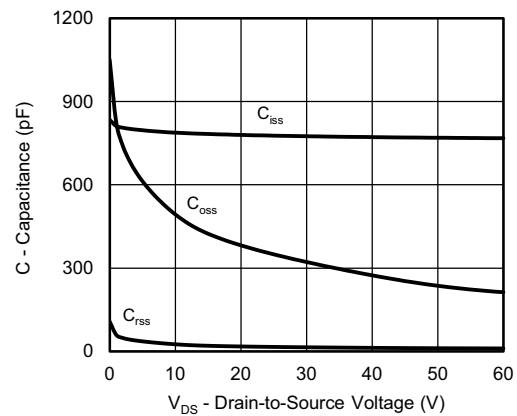
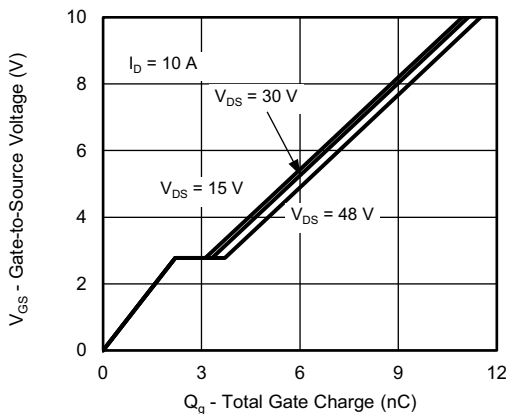
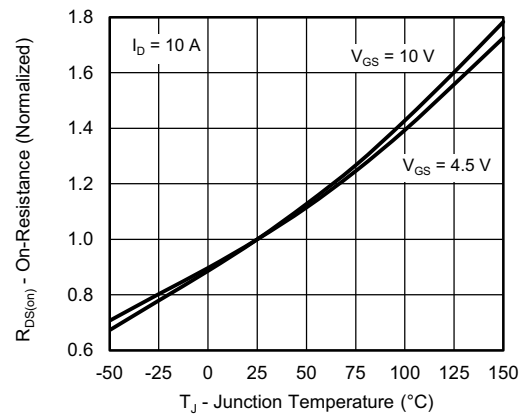


SPECIFICATIONS ($T_J = 25\text{ }^\circ\text{C}$, unless otherwise noted)						
PARAMETER	SYMBOL	TEST CONDITIONS	MIN.	TYP.	MAX.	UNIT
Static						
Drain-source breakdown voltage	V_{DS}	$V_{GS} = 0\text{ V}$, $I_D = 250\text{ }\mu\text{A}$	60	-	-	V
V_{DS} temperature coefficient	$\Delta V_{DS}/T_J$	$I_D = 250\text{ }\mu\text{A}$	-	33	-	mV/ $^\circ\text{C}$
$V_{GS(th)}$ temperature coefficient	$\Delta V_{GS(th)}/T_J$		-	-4.8	-	
Gate-source threshold voltage	$V_{GS(th)}$	$V_{DS} = V_{GS}$, $I_D = 250\text{ }\mu\text{A}$	1	-	2.8	V
Gate-source leakage	I_{GSS}	$V_{DS} = 0\text{ V}$, $V_{GS} = \pm 20\text{ V}$	-	-	100	nA
Zero gate voltage drain current	I_{DSS}	$V_{DS} = 60\text{ V}$, $V_{GS} = 0\text{ V}$	-	-	1	μA
		$V_{DS} = 60\text{ V}$, $V_{GS} = 0\text{ V}$, $T_J = 70\text{ }^\circ\text{C}$	-	-	10	
On-state drain current ^a	$I_{D(on)}$	$V_{DS} \geq 5\text{ V}$, $V_{GS} = 10\text{ V}$	10	-	-	A
Drain-source on-state resistance ^a	$R_{DS(on)}$	$V_{GS} = 10\text{ V}$, $I_D = 10\text{ A}$	-	0.0160	0.0195	Ω
		$V_{GS} = 4.5\text{ V}$, $I_D = 5\text{ A}$	-	0.0200	0.0250	
Forward transconductance ^a	g_{fs}	$V_{DS} = 10\text{ V}$, $I_D = 10\text{ A}$	-	39	-	S
Dynamic ^b						
Input capacitance	C_{ISS}	$V_{DS} = 30\text{ V}$, $V_{GS} = 0\text{ V}$, $f = 1\text{ MHz}$	-	790	-	pF
Output capacitance	C_{OSS}		-	330	-	
Reverse transfer capacitance	C_{RSS}		-	14	-	
Total gate charge	Q_g	$V_{DS} = 30\text{ V}$, $V_{GS} = 10\text{ V}$, $I_D = 5\text{ A}$	-	11.1	17	nC
		$V_{DS} = 30\text{ V}$, $V_{GS} = 4.5\text{ V}$, $I_D = 5\text{ A}$	-	5.2	8	
Gate-source charge	Q_{gs}		-	2.2	-	
Gate-drain charge	Q_{gd}		-	1.1	-	
Gate resistance	R_g	$f = 1\text{ MHz}$	0.1	0.6	1.2	Ω
Turn-on delay time	$t_{d(on)}$	$V_{DD} = 30\text{ V}$, $R_L = 6\text{ }\Omega$, $I_D \cong 5\text{ A}$, $V_{GEN} = 10\text{ V}$, $R_g = 1\text{ }\Omega$	-	7	15	ns
Rise time	t_r		-	21	40	
Turn-off delay time	$t_{d(off)}$		-	10	20	
Fall time	t_f		-	10	20	
Turn-on delay time	$t_{d(on)}$	$V_{DD} = 30\text{ V}$, $R_L = 6\text{ }\Omega$, $I_D \cong 5\text{ A}$, $V_{GEN} = 4.5\text{ V}$, $R_g = 1\text{ }\Omega$	-	13	25	
Rise time	t_r		-	25	50	
Turn-off delay time	$t_{d(off)}$		-	10	20	
Fall time	t_f		-	22	45	
Drain-Source Body Diode Characteristics						
Continuous source-drain diode current	I_S	$T_C = 25\text{ }^\circ\text{C}$	-	-	3.8	A
Pulse diode forward current	I_{SM}		-	-	40	
Body diode voltage	V_{SD}	$I_S = 5\text{ A}$, $V_{GS} = 0\text{ V}$	-	0.79	1.2	V
Body diode reverse recovery time	t_{rr}	$I_F = 5\text{ A}$, $di/dt = 100\text{ A}/\mu\text{s}$, $T_J = 25\text{ }^\circ\text{C}$	-	30	60	ns
Body diode reverse recovery charge	Q_{rr}		-	60	120	nC
Reverse recovery fall time	t_a		-	15	-	ns
Reverse recovery rise time	t_b		-	15	-	

Notes

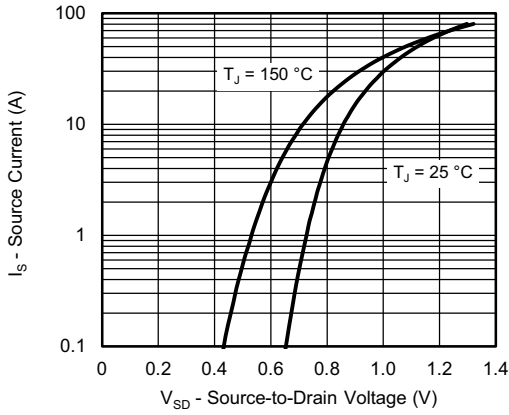
- a. Pulse test; pulse width $\leq 300\text{ }\mu\text{s}$, duty cycle $\leq 2\%$
b. Guaranteed by design, not subject to production testing

Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

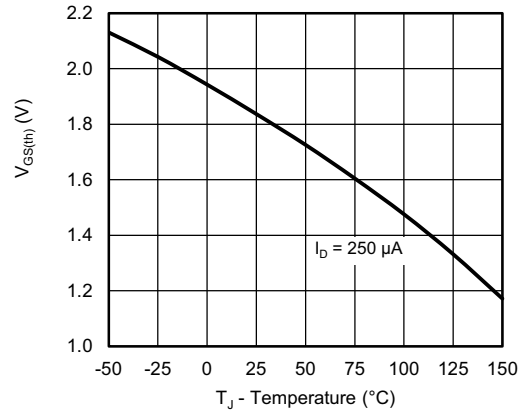
TYPICAL CHARACTERISTICS (25 °C, unless otherwise noted)

Output Characteristics

Transfer Characteristics

On-Resistance vs. Drain Current and Gate Voltage

Capacitance

Gate Charge

On-Resistance vs. Junction Temperature



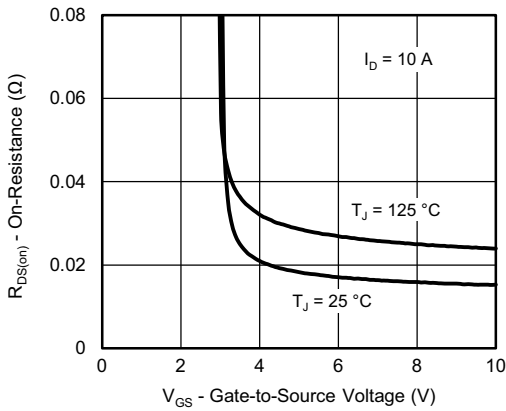
TYPICAL CHARACTERISTICS (25 °C, unless otherwise noted)



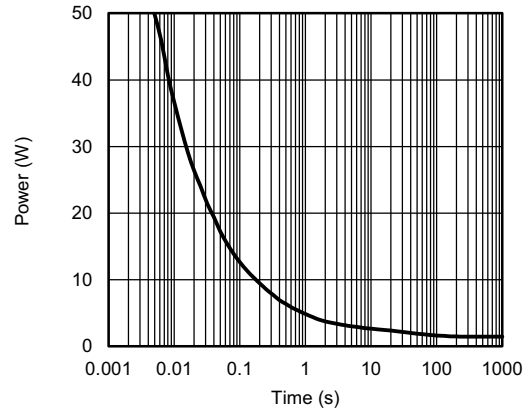
Source-Drain Diode Forward Voltage



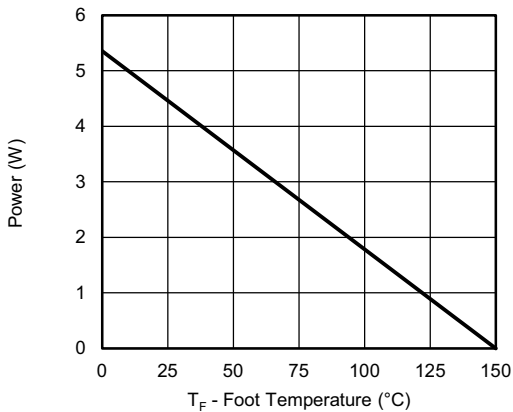
Threshold Voltage



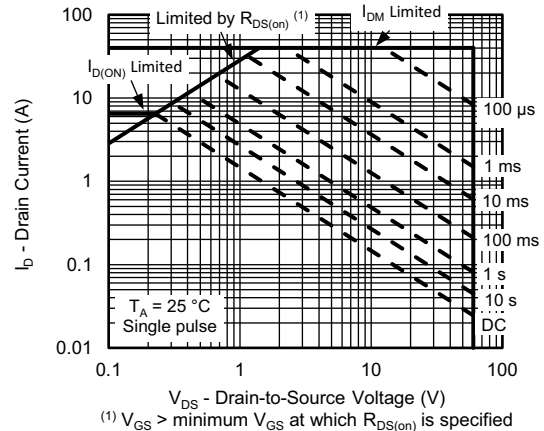
On-Resistance vs. Gate-to-Source Voltage



Single Pulse Power, Junction-to-Ambient

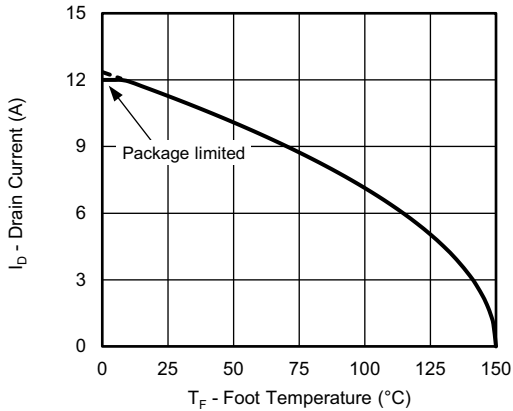


Power, Junction-to-Foot



Safe Operating Area, Junction-to-Ambient

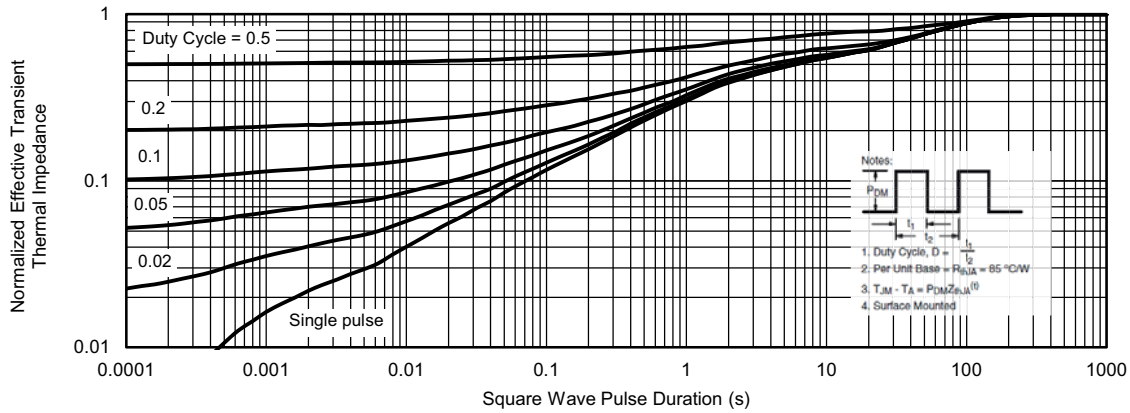
TYPICAL CHARACTERISTICS (25 °C, unless otherwise noted)



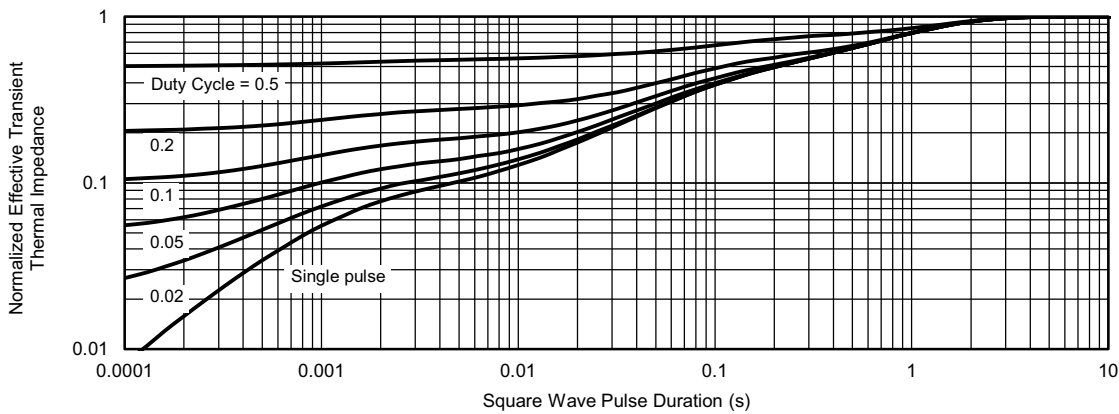
Note

a. The power dissipation P_D is based on T_J max. = 150 °C, using junction-to-case thermal resistance, and is more useful in settling the upper dissipation limit for cases where additional heatsinking is used. It is used to determine the current rating, when this rating falls below the package limit.

Current Derating ^a



Normalized Thermal Transient Impedance, Junction-to-Ambient



Normalized Thermal Transient Impedance, Junction-to-Foot

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